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May 2016

MOCD207M, MOCD208M, MOCD211M, MOCD213M, MOCD217M 8-pin SOIC Dual-Channel Phototransistor Output Optocoupler

Features

- Closely Matched Current Transfer Ratios
- Minimum BV_{CEO} of 70 V Guaranteed
 - MOCD207M, MOCD208M
- Minimum BV_{CEO} of 30 V Guaranteed
 - MOCD211M, MOCD213M, MOCD217M
- Low LED Input Current Required for Easier Logic Interfacing
 - MOCD217M
- Convenient Plastic SOIC-8 Surface Mountable Package Style, with 0.050" Lead Spacing
- Safety and Regulatory Approvals:
 - UL1577, 2,500 VAC_{RMS} for 1 Minute
 - DIN-EN/IEC60747-5-5, 565 V Peak Working Insulation Voltage

Applications

- Feedback Control Circuits
- Interfacing and Coupling Systems of Different Potentials and Impedances
- General Purpose Switching Circuits
- Monitor and Detection Circuits

Description

These devices consist of two gallium arsenide infrared emitting diodes optically coupled to two monolithic silicon phototransistor detectors, in a surface mountable, small outline, plastic package. They are ideally suited for high-density applications, and eliminate the need for through-the-board mounting.

Schematic

ANODE 1 1 8 COLLECTOR 1 CATHODE 1 2 7 EMITTER 1 ANODE 2 3 6 COLLECTOR 2 CATHODE 2 4 5 EMITTER 2

Figure 1. Schematic

Package Outline

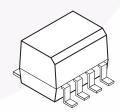


Figure 2. Package Outline

Safety and Insulation Ratings

As per DIN EN/IEC 60747-5-5, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Parameter		Characteristics
Installation Classifications per DIN VDE	cations per DIN VDE < 150 V _{RMS}	
0110/1.89 Table 1, For Rated Mains Voltage	< 300 V _{RMS}	I–III
Climatic Classification		55/100/21
Pollution Degree (DIN VDE 0110/1.89)		2
Comparative Tracking Index		175

Symbol	Parameter	Value	Unit
V	Input-to-Output Test Voltage, Method A, $V_{IORM} \times 1.6 = V_{PR}$, Type and Sample Test with $t_m = 10$ s, Partial Discharge < 5 pC	904	V _{peak}
V _{PR}	Input-to-Output Test Voltage, Method B, $V_{IORM} \times 1.875 = V_{PR}$, 100% Production Test with $t_m = 1$ s, Partial Discharge < 5 pC	1060	V _{peak}
V _{IORM}	Maximum Working Insulation Voltage	565	V _{peak}
V _{IOTM}	Highest Allowable Over-Voltage	4000	V _{peak}
	External Creepage	≥ 4	mm
	External Clearance	≥ 4	mm
DTI	Distance Through Insulation (Insulation Thickness)	≥ 0.4	mm
T _S	Case Temperature ⁽¹⁾	150	°C
I _{S,INPUT}	Input Current ⁽¹⁾	200	mA
P _{S,OUTPUT}	Output Power ⁽¹⁾	300	mW
R _{IO}	Insulation Resistance at T _S , V _{IO} = 500 V ⁽¹⁾	> 10 ⁹	Ω

Note:

1. Safety limit values – maximum values allowed in the event of a failure.

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. $T_A = 25^{\circ}$ C unless otherwise specified.

Symbol	Rating	Value	Unit
TOTAL DEVI	CE		
T _{STG}	Storage Temperature	-40 to +125	°C
T _A	Ambient Operating Temperature	-40 to +100	°C
T _J	Junction Temperature	-40 to +125	°C
T _{SOL}	Lead Solder Temperature	260 for 10 seconds	°C
Ъ	Total Device Power Dissipation @ T _A = 25°C	240	mW
P_{D}	Derate Above 25°C	2.94	mW/°C
EMITTER			
I _F	Continuous Forward Current	60	mA
I _F (pk)	Forward Current – Peak (PW = 100 µs, 120 pps)	1.0	Α
V_{R}	Reverse Voltage	6.0	V
В	LED Power Dissipation @ T _A = 25°C	90	mW
P_{D}	Derate Above 25°C	0.8	mW/°C
DETECTOR			
I _C	Continuous Collector Current	150	mA
	Collector-Emitter Voltage		
V_{CEO}	MOCD207M, MOCD208M, MOCD213M	70	V
	MOCD211M, MOCD217M	30	V
V _{ECO}	Emitter-Collector Voltage	7	V
В	Detector Power Dissipation @ T _A = 25°C	150	mW
P_{D}	Derate Above 25°C	1.76	mW/°C

Electrical Characteristics

 $T_A = 25$ °C unless otherwise specified.

Symbol	Parameter	Device	Test Conditions	Min.	Тур.	Max.	Unit
EMITTER	<u>.</u>	ı	I.	I	1		
		MOCD217M	I _F = 1 mA		1.05	1.3	V
		MOCD213M	I _F = 10 mA		1.15	1.5	V
V _F	Input Forward Voltage	MOCD207M, MOCD208M, MOCD211M	I _F = 30 mA		1.25	1.5	V
I _R	Reverse Leakage Current	All	V _R = 6 V		0.001	100	μΑ
C _{IN}	Input Capacitance	All			18		pF
DETECTO	OR						
	0 11 / 5 11 5 10 /	A.II	V _{CE} = 10 V, T _A = 25°C		1.0	50	nA
I _{CEO}	Collector-Emitter Dark Current	All	$V_{CE} = 10 \text{ V}, T_{A} = 100^{\circ}\text{C}$		1.0		μΑ
	Collector Emitter Progledown	MOCD211M, MOCD217M	I _C = 100 μA	30	100		V
BV _{CEO}	Collector-Emitter Breakdown Voltage	MOCD207M, MOCD208M, MOCD213M	Ι _C = 100 μΑ	70	100		V
BV _{ECO}	Emitter-Collector Breakdown Voltage	All	Ι _Ε = 100 μΑ	7	10		V
C _{CE}	Collector-Emitter Capacitance	All	f = 1.0 MHz, V _{CE} = 0		7		pF
COUPLE	D						
		MOCD207M	$I_F = 10 \text{ mA}, V_{CE} = 5 \text{ V}$	100		200	%
		MOCD208M	$I_F = 10 \text{ mA}, V_{CE} = 5 \text{ V}$	40		125	%
CTR	Collector-Output Current	MOCD211M	$I_F = 10 \text{ mA}, V_{CE} = 5 \text{ V}$	20			%
		MOCD213M	$I_F = 10 \text{ mA}, V_{CE} = 5 \text{ V}$	100			%
		MOCD217M	$I_F = 1 \text{ mA}, V_{CE} = 5 \text{ V}$	100			%
V _{CE(SAT)}	Collector-Emitter Saturation Voltage	MOCD207M, MOCD208M, MOCD211M, MOCD213M	I _C = 2 mA, I _F = 10 mA	4		0.4	V
		MOCD217M	$I_C = 100 \mu A, I_F = 1 mA$			0.4	V
t _{on}	Turn-On Time	All	$I_C = 2 \text{ mA}, V_{CC} = 10 \text{ V},$ $R_L = 100 \Omega \text{ (Figure 8)}$		7.5		μs
t _{off}	Turn-Off Time	All	$I_C = 2 \text{ mA}, V_{CC} = 10 \text{ V},$ $R_L = 100 \Omega \text{ (Figure 8)}$		5.7		μs
t _r	Rise Time	All	$I_C = 2 \text{ mA}, V_{CC} = 10 \text{ V},$ $R_L = 100 \Omega \text{ (Figure 8)}$		3.2		μs
t _f	Fall Time	All	$I_C = 2 \text{ mA}, V_{CC} = 10 \text{ V},$ $R_L = 100 \Omega \text{ (Figure 8)}$		4.7		μs

Electrical Characteristics

 $T_A = 25$ °C unless otherwise specified.

Isolation Characteristics

Symbol	Characteristic	Test Conditions	Min.	Тур.	Max.	Unit
V _{ISO}	Input-Output Isolation Voltage	t = 1 Minute	2500			VAC _{RMS}
C _{ISO}	Isolation Capacitance	$V_{I-O} = 0 \text{ V, } f = 1 \text{ MHz}$		0.2		pF
R _{ISO}	Isolation Resistance	$V_{I-O} = \pm 500 \text{ VDC}, T_A = 25^{\circ}\text{C}$	10 ¹¹			Ω

Typical Performance Curves

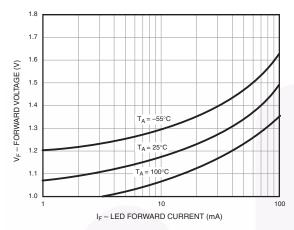


Figure 3. LED Forward Voltage vs. Forward Current

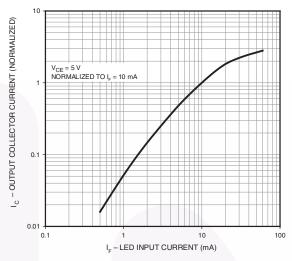


Figure 4. Output Curent vs. Input Current

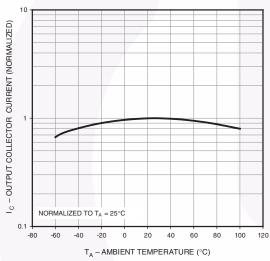


Figure 5. Output Current vs. Ambient Temperature

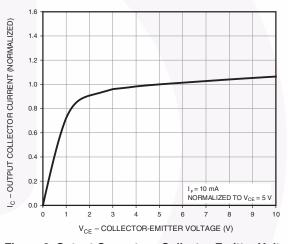


Figure 6. Output Current vs. Collector-Emitter Voltage

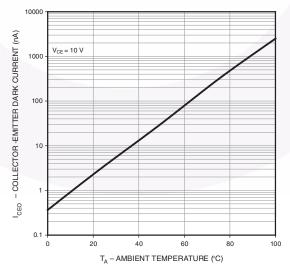
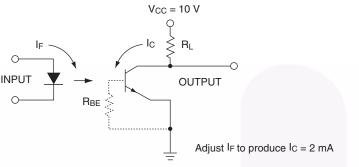


Figure 7. Dark Current vs. Ambient Temperature

Switching Time Test Circuit and Waveforms



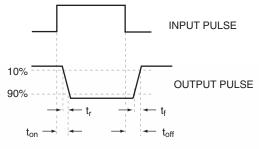


Figure 8. Switching Time Test Circuit and Waveforms

Reflow Profile

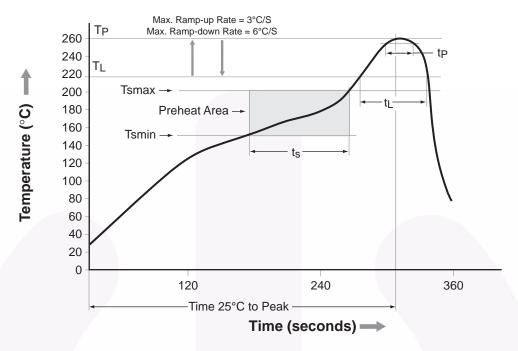


Figure 9. Reflow Profile

Profile Freature	Pb-Free Assembly Profile	
Temperature Minimum (Tsmin)	150°C	
Temperature Maximum (Tsmax)	200°C	
Time (t _S) from (Tsmin to Tsmax)	60-120 seconds	
Ramp-up Rate (t _L to t _P)	3°C/second maximum	
Liquidous Temperature (T _L)	217°C	
Time (t _L) Maintained Above (T _L)	60-150 seconds	
Peak Body Package Temperature	260°C +0°C / -5°C	
Time (t _P) within 5°C of 260°C	30 seconds	
Ramp-down Rate (T _P to T _L)	6°C/second maximum	
Time 25°C to Peak Temperature	8 minutes maximum	

Ordering Information(2)

Part Number	Package	Packing Method
MOCD207M	Small Outline 8-Pin	Tube (100 Units)
MOCD207R2M	Small Outline 8-Pin	Tape and Reel (2500 Units)
MOCD207VM	Small Outline 8-Pin, DIN EN/IEC60747-5-5 Option	Tube (100 Units)
MOCD207R2VM	Small Outline 8-Pin, DIN EN/IEC60747-5-5 Option	Tape and Reel (2500 Units)

Note:

2. The product orderable part number system listed in this table also applies to the MOCD208M, MOCD211M, MOCD213M, and MOCD217M products.

Marking Information

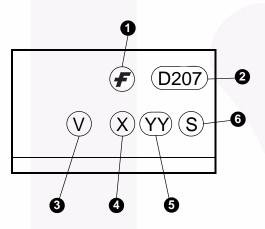
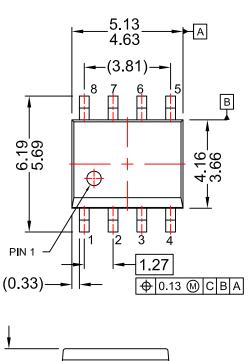
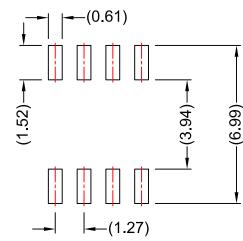


Figure 10. Top Mark

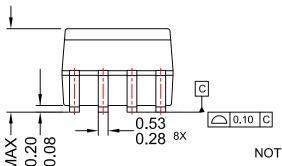
Table 1. Top Mark Definitions

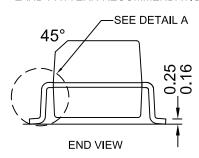
1	Fairchild Logo
2	Device Number
3	DIN EN/IEC60747-5-5 Option (only appears on component ordered with this option)
4	One-Digit Year Code, e.g., "4"
5	Digit Work Week, Ranging from "01" to "53"
6	Assembly Package Code





LAND PATTERN RECOMMENDATION



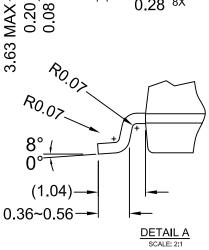






- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS DO NOT INCLUDE MOLD FLASH OR BURRS.
- D) LANDPATTERN STANDARD: SOIC127P600X175-8M.
- E) DRAWING FILENAME: MKT-M08Erev5





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